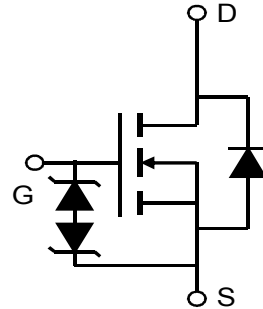


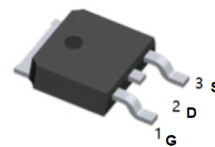
### General Description

- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Eoss
- ESD protected
- RoHS and Halogen-Free Compliant



### Product Summary

$V_{DS}$	60V
$I_D$ (at $V_{GS}=10V$ )	46A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 9.5m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 13.3m $\Omega$



TO-252(DPAK) top view

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>G</sup>	$T_C=25^\circ\text{C}$	$I_D$	46	A
	$T_C=100^\circ\text{C}$		36.5	
Pulsed Drain Current <sup>C</sup>		$I_{DM}$	110	
Continuous Drain Current	$T_A=25^\circ\text{C}$	$I_{DSM}$	19	A
	$T_A=70^\circ\text{C}$		15	
Avalanche Current <sup>C</sup>		$I_{AS}$	17	A
Avalanche energy $L=0.3\text{mH}$ <sup>C</sup>		$E_{AS}$	43	mJ
$V_{DS}$ Spike <sup>I</sup>	10 $\mu\text{s}$	$V_{SPIKE}$	72	V
Power Dissipation <sup>B</sup>	$T_C=25^\circ\text{C}$	$P_D$	59.5	W
	$T_C=100^\circ\text{C}$		23.5	
Power Dissipation <sup>A</sup>	$T_A=25^\circ\text{C}$	$P_{DSM}$	6.2	W
	$T_A=70^\circ\text{C}$		4.0	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10\text{s}$	$R_{\theta JA}$	15	20	$^\circ\text{C/W}$
	Steady-State		40	50	$^\circ\text{C/W}$
Maximum Junction-to-Case		$R_{\theta JC}$	1.7	2.1	$^\circ\text{C/W}$

### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1	μA
					5	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.4	1.8	2.4	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		7.7	9.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		10.3	13.3	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		52		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.72	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current <sup>G</sup>				46	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, f=1MHz		1100		pF
C <sub>oss</sub>	Output Capacitance			300		pF
C <sub>riss</sub>	Reverse Transfer Capacitance			28		pF
R <sub>g</sub>	Gate resistance	f=1MHz	0.6	1.2	2.0	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =20A		14.5	25	nC
Q <sub>g(4.5V)</sub>	Total Gate Charge			7	13	nC
Q <sub>gs</sub>	Gate Source Charge			2.5		nC
Q <sub>gd</sub>	Gate Drain Charge			3.5		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, R <sub>L</sub> =1.5Ω, R <sub>GEN</sub> =3Ω		6.5		ns
t <sub>r</sub>	Turn-On Rise Time			3.5		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			22		ns
t <sub>f</sub>	Turn-Off Fall Time			3		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, di/dt=500A/μs		19		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, di/dt=500A/μs		65		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

I. The spike duty cycle 5% max, limited by junction temperature T<sub>J(MAX)</sub>=125° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

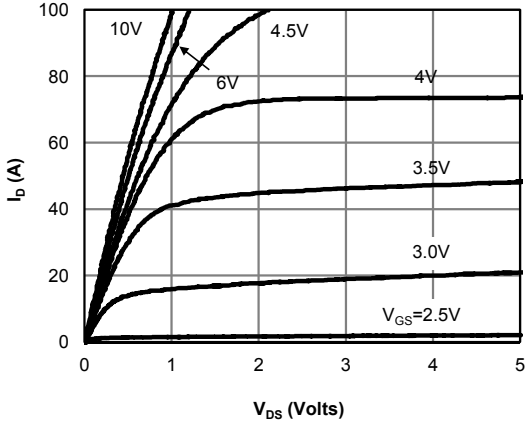


Figure 1: On-Region Characteristics (Note E)

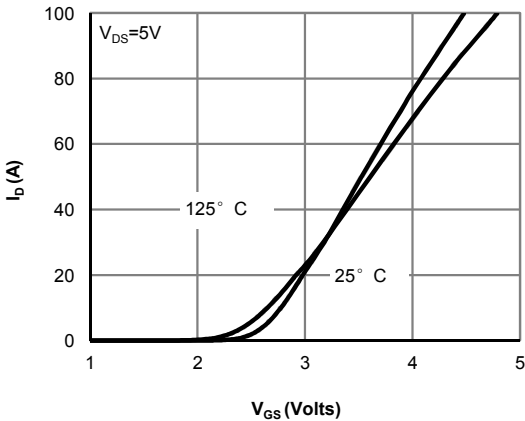


Figure 2: Transfer Characteristics (Note E)

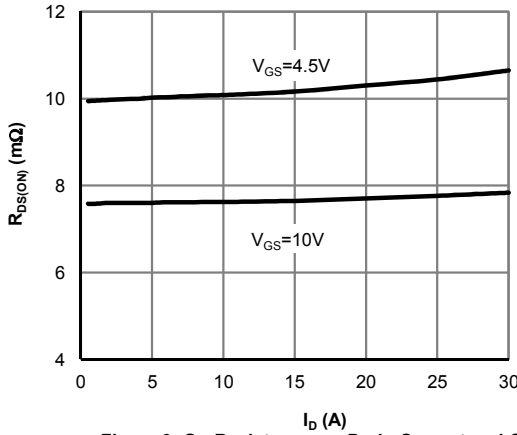


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

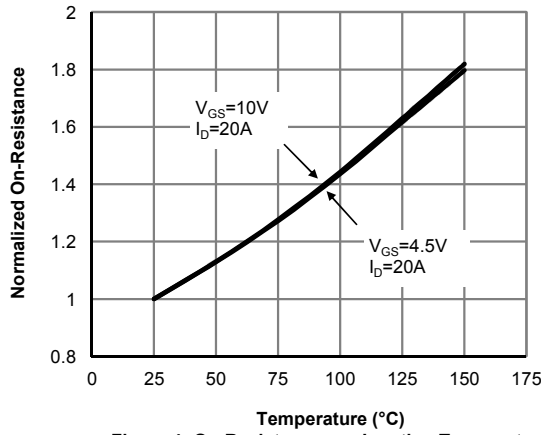


Figure 4: On-Resistance vs. Junction Temperature (Note E)

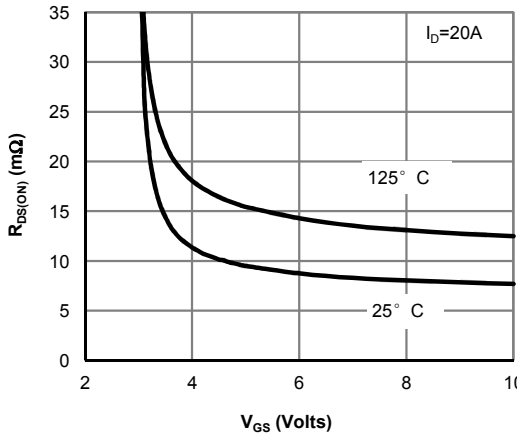


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

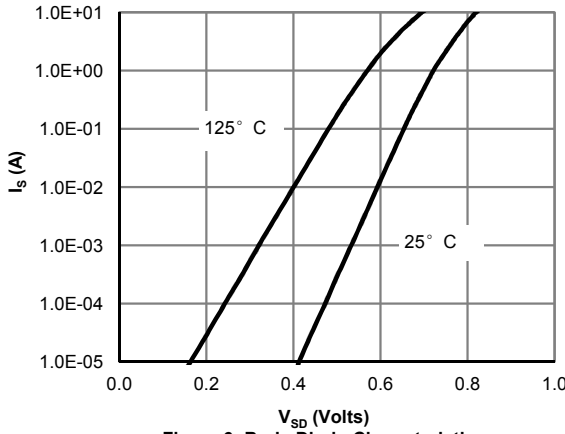


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

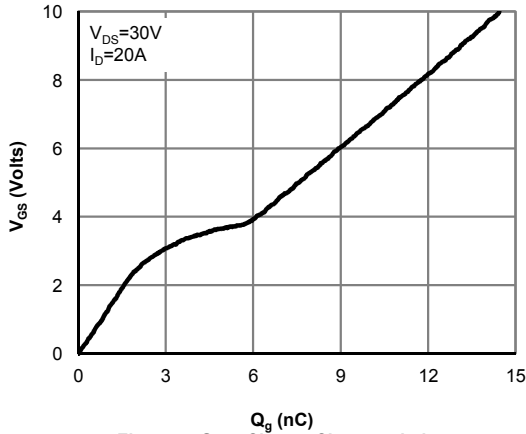


Figure 7: Gate-Charge Characteristics

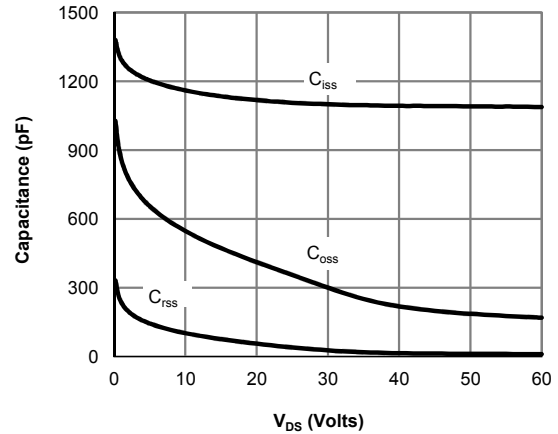


Figure 8: Capacitance Characteristics

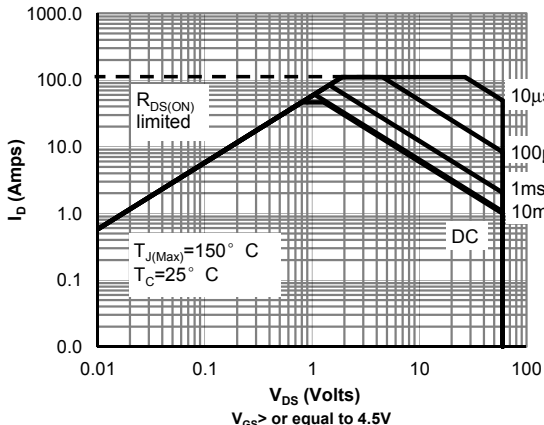


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

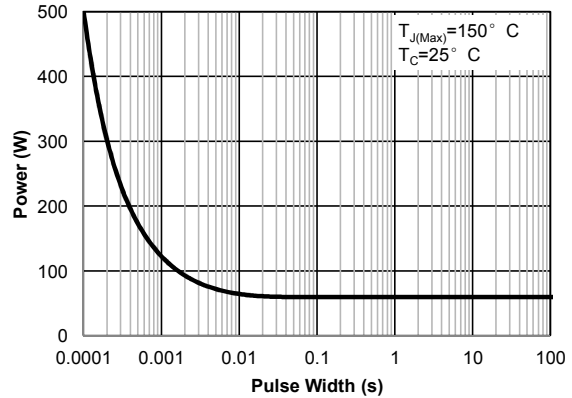


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

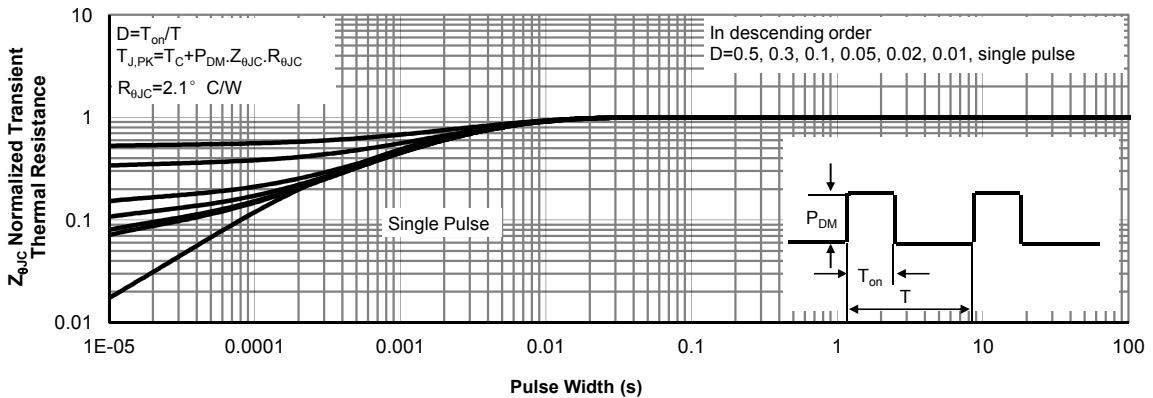


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

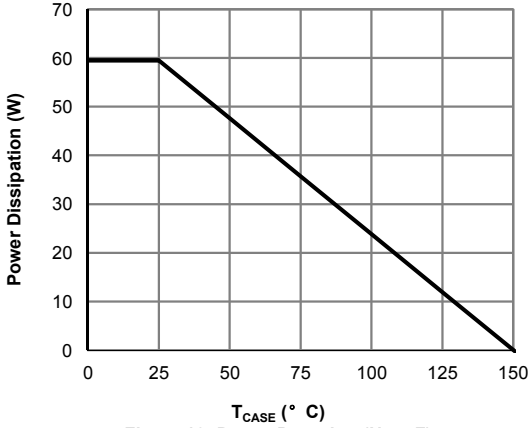


Figure 12: Power De-rating (Note F)

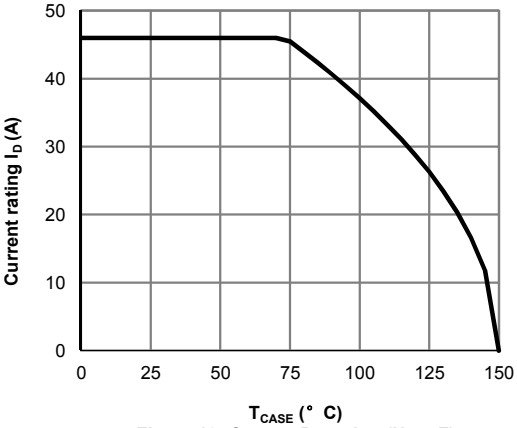


Figure 13: Current De-rating (Note F)

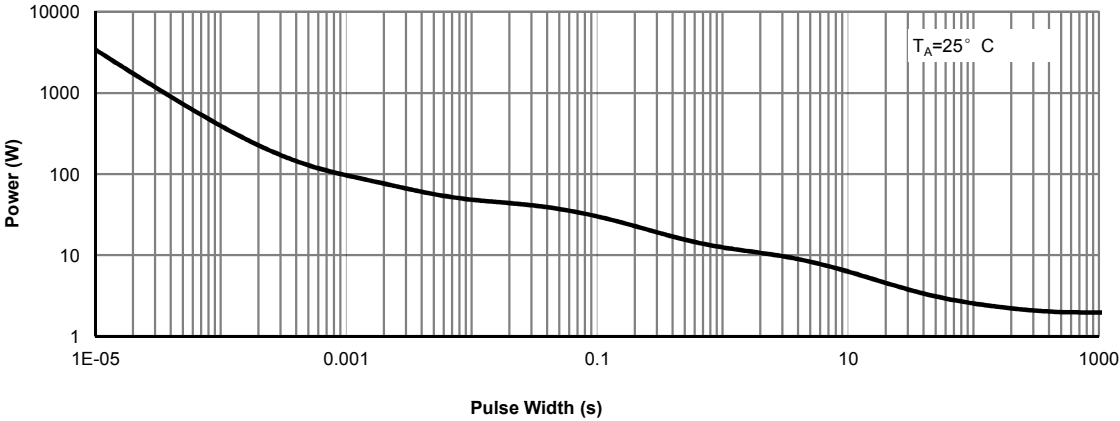


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

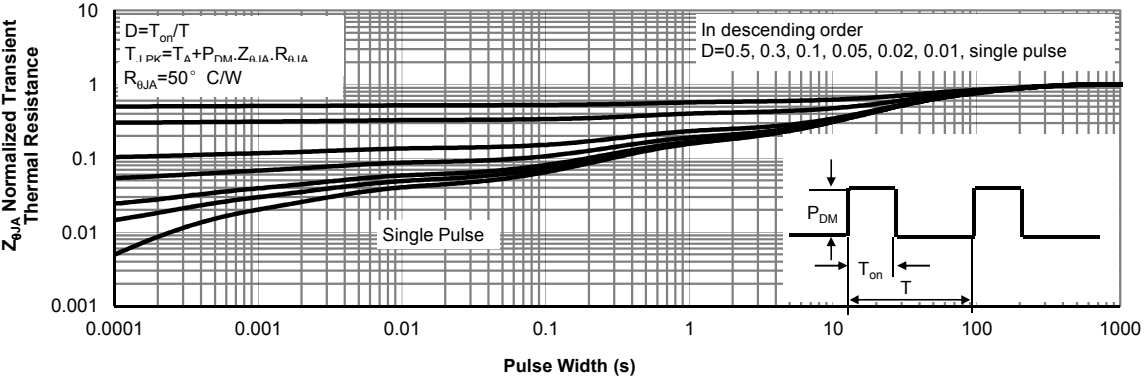


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

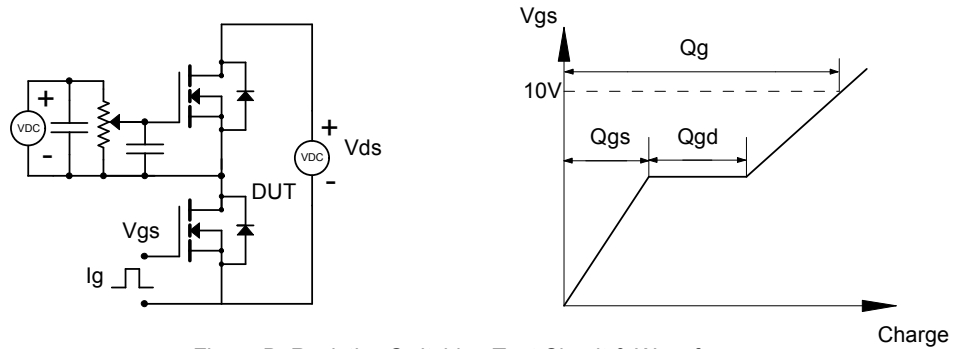


Figure B: Resistive Switching Test Circuit & Waveforms

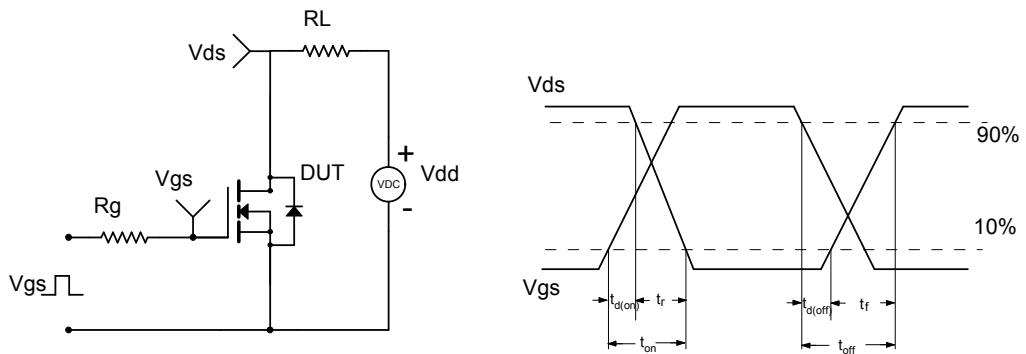


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

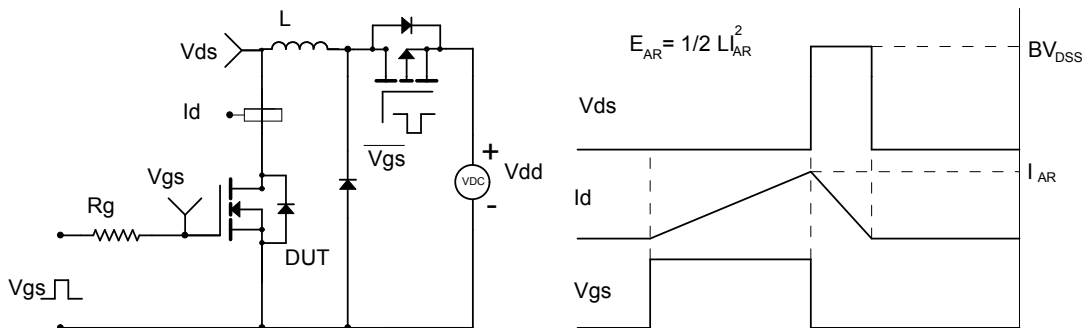
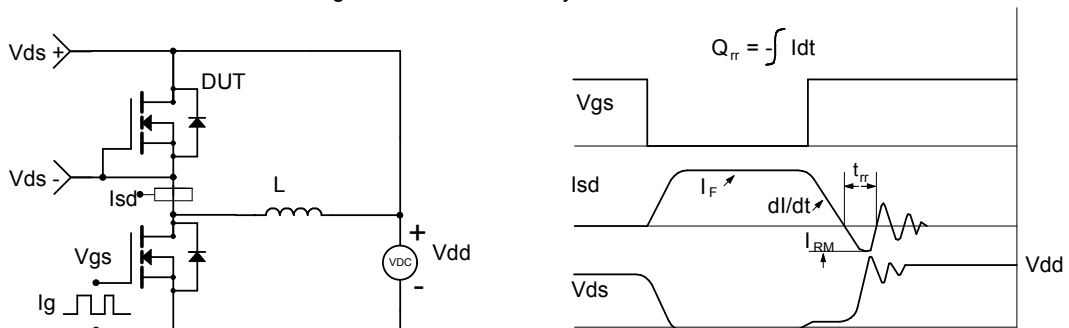
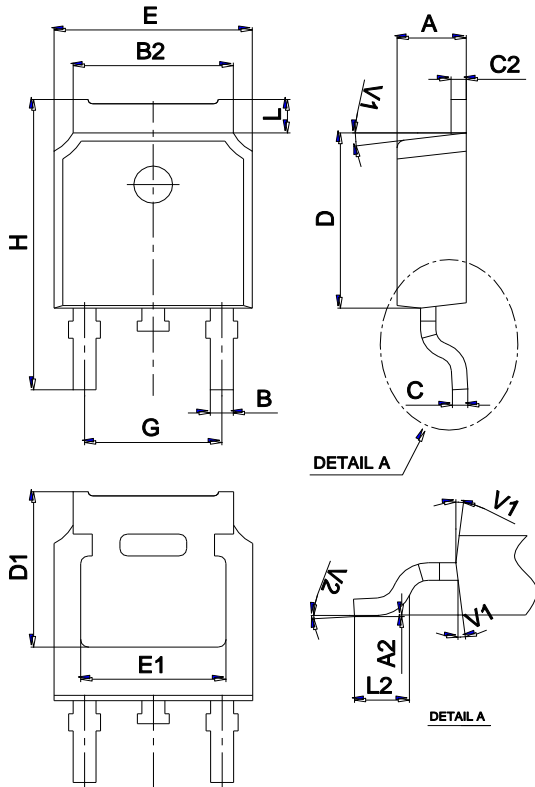


Figure D: Diode Recovery Test Circuit & Waveforms



Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Ordering information

Order code	Package	Baseqty	Delivery mode
UMW AOD2610E	TO-252	2500	Tape and reel

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